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PUBLICATIONS:

2020

1. Y. M. Aneesh and B. Bindu, "A Physics-based Single Event Transient Pulse Width Model for CMOS VLSI Circuits," in IEEE Transactions on Device and Materials Reliability, *doi: 10.1109/TDMR.2020.3023285*.
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7. SR Sriram, B Bindu, "A physics-based model for LER-induced threshold voltage variations in double-gate MOSFET," Journal of Computational Electronics, Vol 19,Issue 2,pp.622-630,2020

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